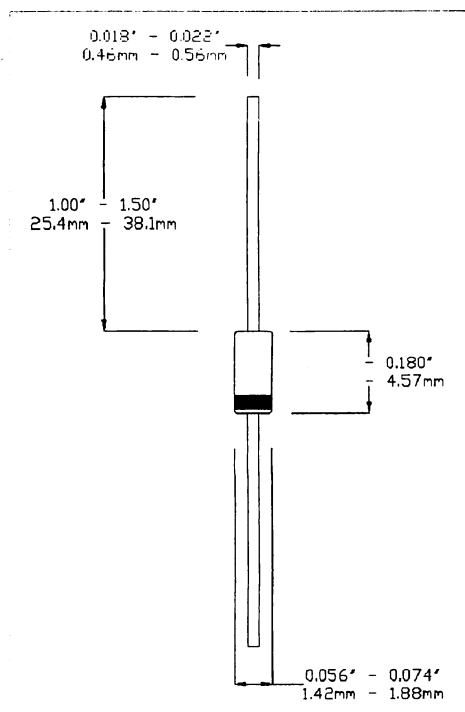


1N645-1

FEATURES

- 1N645-1
- SILICON RECTIFIER
- METALLURGICALLY BONDED
- HERMETICALLY SEALED



MAXIMUM RATINGS AT 25 °C

Operating Temperature:	-65°C to +175°C
Storage Temperature:	-65°C to +175°C
Surge Current A, sine 8.3mS:	5.0A
Total Power Dissipation:	500mW
Operating Current:	400mA, T _A = +25°C
Operating Current:	150mA, T _A = +150°C
Derating Factor:	2mA/°C above +25°C
Derating Factor:	6mA/°C above +150°C
D.C. Reverse Voltage (VRWM):	225V

DC ELECTRICAL CHARACTERISTICS

V _F				I _R			
Ambient (°C)	I _F mA	Min V	Max V	Ambient (°C)	V _R V (dc)	Min μA	Max μA
25	400	0.80	1.00	25	225	-	0.050
150	400	0.70	0.95	25	270(ac)	-	50
-55	400	-	1.20	150	225	-	25

DESIGN DATA

Case: Hermetically sealed glass package
DO-35 outline

Lead Material: Copper clad steel

Lead Finish: Tin/Lead

Thermal Resistance (R_{θJL}): 250°C/W maximum
at L=0.375"

Thermal Impedance (Z_{θJX}): 35°C/W maximum

Marking: Blue body coat, Black digits.

Polarity: Cathode end is banded.

AC ELECTRICAL CHARACTERISTICS AT 25°C

	Symbol	Min	Max
Capacitance @ V _R = 4V	pF	-	20



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